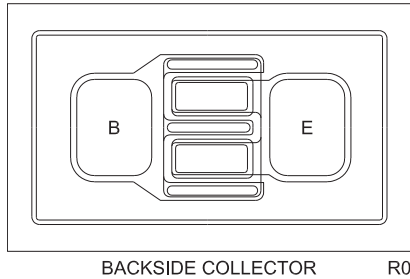


CP396V-2N2369A

NPN - Saturated Switch Transistor Die

0.2 Amp, 40 Volt

The CP396V-2N2369A is a silicon NPN transistor designed for high speed saturated switching applications.



MECHANICAL SPECIFICATIONS:

Die Size	14.2 x 8.7 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Size	2.9 x 3.7 MILS
Emitter Bonding Pad Size	2.9 x 3.7 MILS
Top Side Metalization	Al – 13,000Å
Back Side Metalization	Au-As – 9,000Å
Scribe Alley Width	1.96 MILS
Wafer Diameter	5 INCHES
Gross Die Per Wafer	139,524

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CES}	40	V
Collector-Emmitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	4.5	V
Continuous Collector Current	I_C	200	mA
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$

SYMBOL

UNITS

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=20\text{V}$		400	nA
BV_{CBO}	$I_C=10\mu\text{A}$	40		V
BV_{CES}	$I_C=10\mu\text{A}$	40		V
BV_{CEO}	$I_C=10\text{mA}$	15		V
BV_{EBO}	$I_E=10\mu\text{A}$	4.5		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		200	mV
$V_{CE(SAT)}$	$I_C=30\text{mA}, I_B=3.0\text{mA}$		250	mV
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		500	mV
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	700	850	mV
$V_{BE(SAT)}$	$I_C=30\text{mA}, I_B=3.0\text{mA}$		1.15	V
$V_{BE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		1.6	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	40	120	
h_{FE}	$V_{CE}=0.4\text{V}, I_C=30\text{mA}$	30		
h_{FE}	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	20		
f_T	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	500		MHz
C_{ob}	$V_{CB}=5.0\text{V}, I_E=0, f=140\text{kHz}$		4.0	pF
t_{on}	$V_{CC}=3.0\text{V}, I_C=10\text{mA}, I_{B1}=3.0\text{mA}$		12	ns
t_{off}		$I_{B2}=1.5\text{mA}$	18	ns

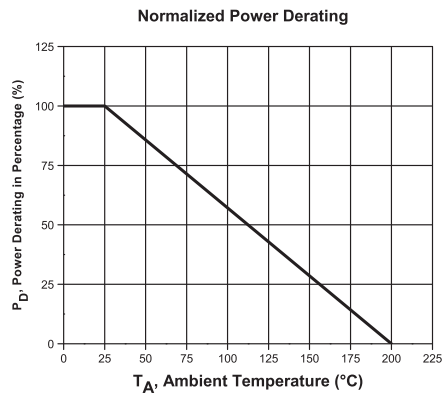
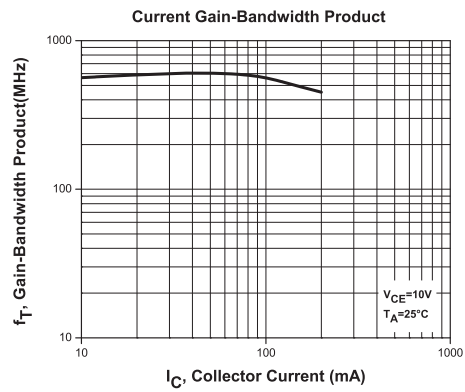
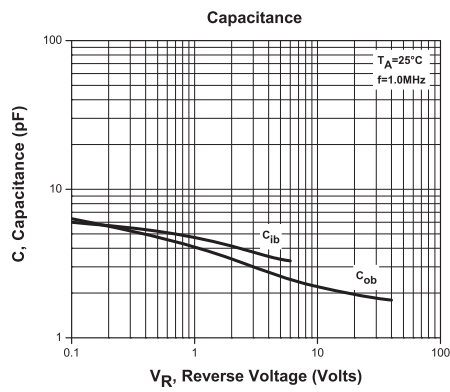
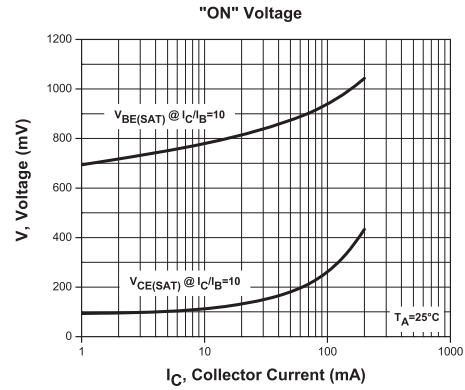
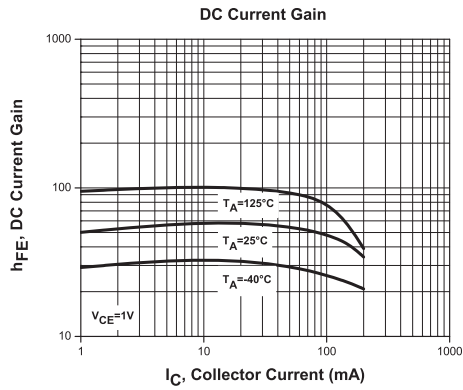
PACKING OPTIONS:

- CP396V-2N2369A-CT: Singulated die in waffle pack; 700 die per tray.
- CP396V-2N2369A-WN: Full wafer, unsawn, 100% tested with reject die inked.
- CP396V-2N2369A-WR: Full wafer, sawn and mounted on plastic ring, 100% tested with reject die inked.

R0 (6-March 2015)

CP396V-2N2369A

Typical Electrical Characteristics



OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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